

Low VF Schottky Diode

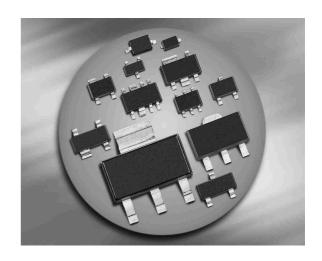
• Reverse voltage: 30 V

• Forward current: 1 A

• Low forward voltage and smallest package form factor $(1.0 \times 0.6 \times 4 \text{ mm})$ for mobile phone battery charger application

• Pb-free (RoHS compliant) package





BAS3010S-02LRH



Туре	Package	Configuration	Marking
BAS3010S-02LRH	TSLP-2-17	single	1T

Maximum Ratings at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Value	Unit	
Diode reverse voltage ¹⁾	V_{R}	30	V	
Forward current ¹⁾ , <i>T</i> _S ≤ 114 °C	I _F	1	Α	
Non-repetitive peak surge forward current	I _{FSM}	4		
(<i>t</i> _p ≤ 10 ms)				
Junction temperature	T _i	150	°C	
Operating temperature range	T _{op}	-55150		
Storage temperature	T _{stq}	-65150		
Storage temperature	T _{stg}	-65150		

Thermal Resistance

Junction - soldering point ²⁾	R _{thJS}	≤ 60	K/W

¹For T_A > 25 °C the derating of V_R and I_F has to be considered

 $^{^2\}mbox{For calculation of }R_{\mbox{\scriptsize thJA}}$ please refer to Application Note Thermal Resistance



Electrical Characteristics at $T_A = 25$ °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Reverse current ¹⁾	I _R				μA
V _R = 10 V		-		30	
V _R = 30 V		-	-	300	
Forward voltage ¹⁾	V _F				mV
$I_{F} = 1 \; mA$		-	200	250	
$I_{\rm F}$ = 100 mA		-	340	390	
$I_{\rm F}$ = 700 mA		_	500	570	
$I_{\rm F}$ = 1000 mA		-	570	650	
AC Characteristics					
Diode capacitance	C _T	_	10	15	pF
$V_{R} = 5 \text{ V}, f = 1 \text{ MHz}$					

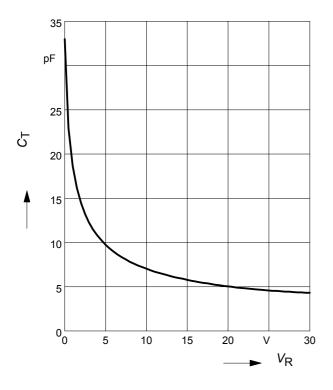
¹Pulsed test: t_p = 300 µs; D = 0.01

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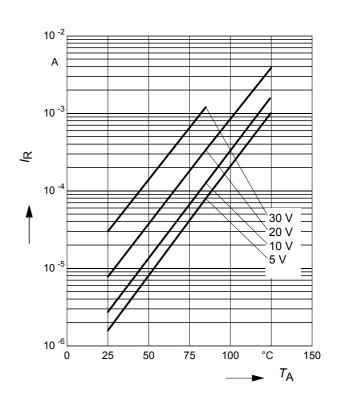
Diode capacitance $C_T = f(V_R)$

f = 1MHz



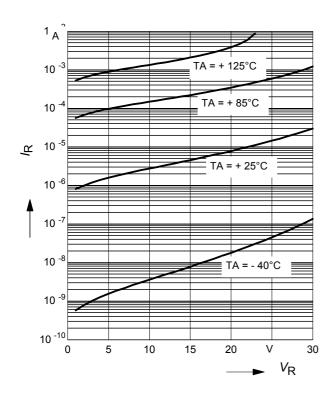
Reverse current $I_R = f(T_A)$

 V_{R} = Parameter



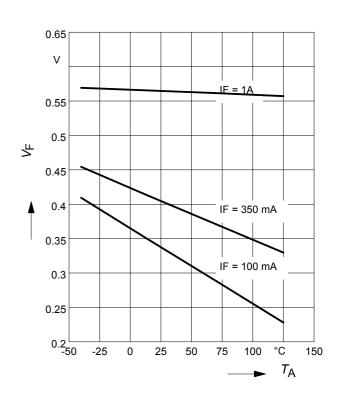
Reverse current $I_R = f(V_R)$

 T_A = Parameter



Forward Voltage $V_F = f(T_A)$

 I_{F} = Parameter



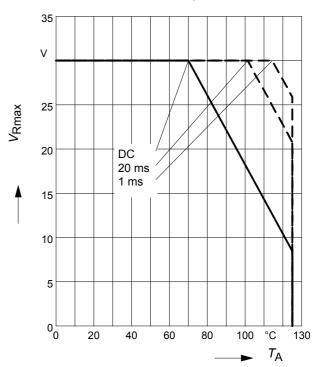


Forward current $I_F = f(V_F)$

10 ⁰ 10 ⁻¹ 10 -2 TA= +125°C +85°C 10 +25°C 40°C 10 10 ⁻⁵ 10 ⁻⁶ 0.3 0.4 0.6 0.2 V_{F}

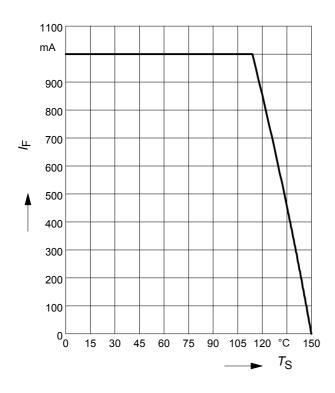
Permissible Reverse voltage $V_R = f(T_A)$ t_p = Paramter, Duty cycle < 0.01

Device mounted on PCB with R_{th} = 160 K/W



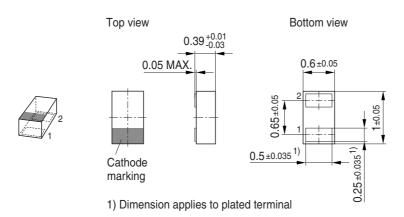
Forward current $I_F = f(T_S)$

BAS3010S-02LRH



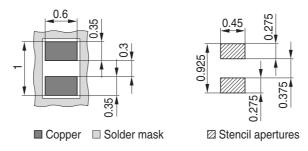


Package Outline

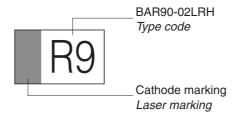


Foot Print

For board assembly information please refer to Infineon website "Packages"

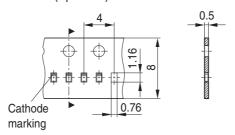


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 15.000 Pieces/Reel Reel ø330 mm = 50.000 Pieces/Reel (optional)



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